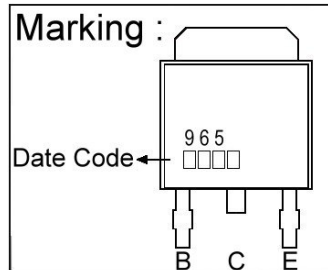
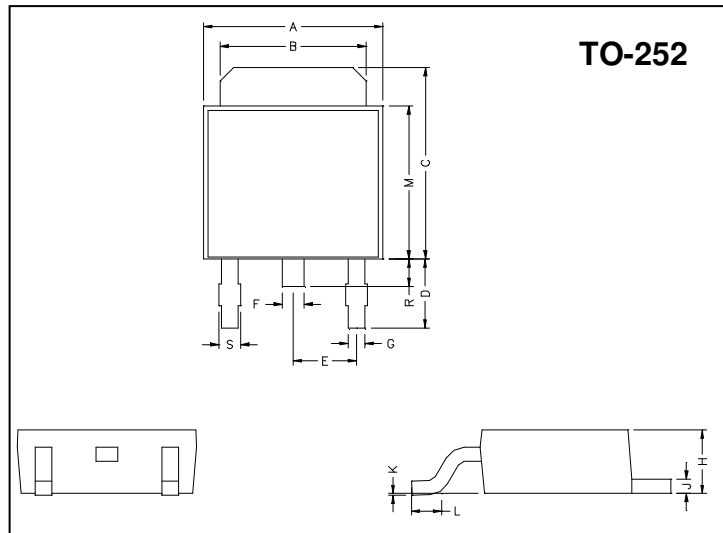


GJ965**NPN EPITAXIAL PLANAR TRANSISTOR****Description**

The GJ965 is designed for use as AF output amplifier and flash unit.

Package Dimensions

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.40	3.00	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CB0}	40	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	7	V
Collector Current (Continuous)	I_C	5	A
Collector Current (Peak $P_T=10\text{ms}$)	I_{CP}	8	A
Junction Temperature	T_j	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$
Total Power Dissipation	P_D	2	W

Electrical Characteristics (Rating at $T_a=25^\circ\text{C}$)

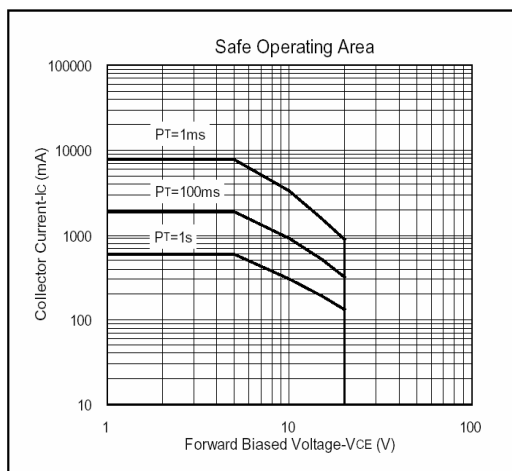
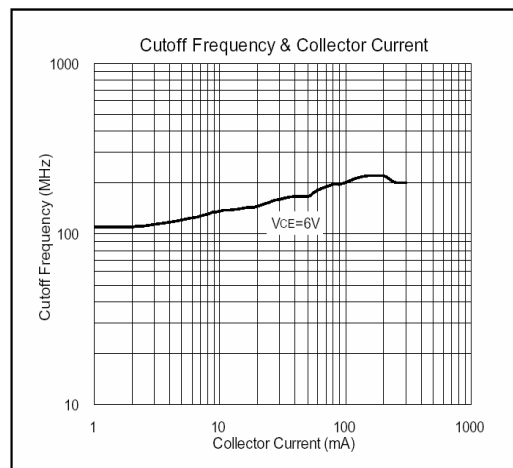
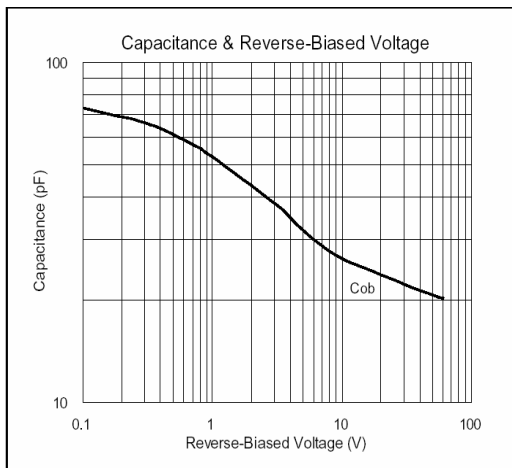
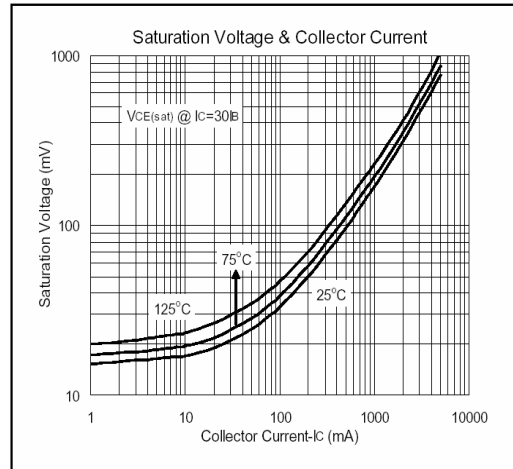
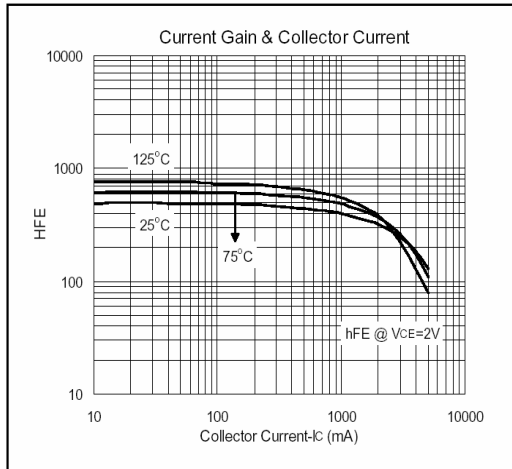
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CB0}	40	-	-	V	$I_C=100\mu\text{A}$
BV_{CEO}	20	-	-	V	$I_C=1\text{mA}$
BV_{EBO}	7	-	-	V	$I_E=10\mu\text{A}$
I_{CBO}	-	-	100	nA	$V_{CB}=60\text{V}$
I_{EBO}	-	-	100	nA	$V_{EB}=7\text{V}$
$*V_{CE(sat)}$	-	350	1000	mV	$I_C=3\text{A}$, $I_B=100\text{mA}$
$*h_{FE1}$	230	-	800		$V_{CE}=2\text{V}$, $I_C=500\text{mA}$
$*h_{FE2}$	150	-	-		$V_{CE}=2\text{V}$, $I_C=2\text{A}$
f_T	-	150	-	MHz	$V_{CE}=6\text{V}$, $I_E=50\text{mA}$
C_{ob}	-	-	50	pF	$V_{CB}=20\text{V}$, $f=1\text{MHz}$

* Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$

Classification Of h_{FE1}

Rank	Q	R	S
Range	230 ~ 380	340 ~ 600	560 ~ 800

Characteristics Curve



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